

Features

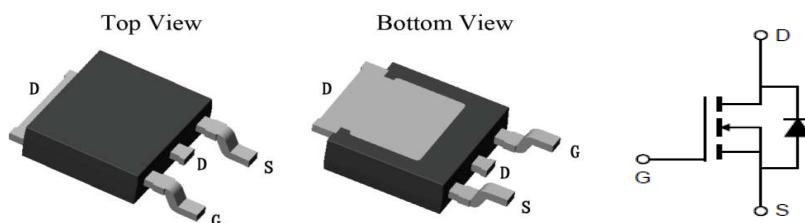
- CRM(CQ) Super_Junction technology
- Much lower Ron*A performance for On-state efficiency
- Much lower FOM for fast switching efficiency

Product Summary

VDS	650V
R _{DS(on)} _typ	0.39Ω
I _D	11A

Applications

- LED/LCD/PDP TV and monitor Lighting
- Solar/Renewable/UPS-Micro Inverter System
- Charger
- Power Supply

100% Avalanche Tested**Package Marking and Ordering Information**

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRJD390N65GC	-	TO-252	Tape&Reel	N/A	N/A	2500pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DS}	650	V
Continuous drain current T _C = 25°C	I _D	11	A
T _C = 100°C		7.0	
Pulsed drain current (T _C = 25°C, t _p limited by T _{jmax})	I _D pulse	44	A
Avalanche energy, single pulse (L=60mH, R _g =30Ω)	E _{AS}	120	mJ
Gate-Source voltage	V _{GS}	±30	V
Power dissipation (T _C = 25°C)	P _{tot}	74	W
Operating junction and storage temperature	T _j , T _{stg}	-55...+150	°C

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case. Max	R _{thJC}	1.68	°C/W
Thermal resistance, junction – ambient. Max	R _{thJA}	73	

Electrical Characteristic (at T_j = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV _{DSS}	650	-	-	V	V _{GS} =0V, I _D =250μA
Gate threshold voltage	V _{GS(th)}	3.5	-	4.5	V	V _{DS} =V _{GS} , I _D =250μA
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =650V, V _{GS} =0V T _C =25°C T _C =150°C
Gate-source leakage current	I _{GSS}	-	0.3	80	nA	V _{GS} =±30V, V _{DS} =0V
Drain-source on-state resistance	R _{DS(on)}	-	0.39	0.45	Ω	V _{GS} =10V, I _D =5.5A, T _C =25°C T _C =150°C
Transconductance	g _{fs}	-	12	-	S	V _{DS} =20V, I _D =5.5A

Dynamic Characteristic

Input Capacitance	C _{iss}	-	770	-	pF	V _{GS} =0V, V _{DS} =100V, f=1MHz
Output Capacitance	C _{oss}	-	32	-		
Reverse Transfer Capacitance	C _{rss}	-	23	-		
Gate Total Charge	Q _G	-	22	-	nC	V _{GS} =10V, V _{DS} =480V, I _D =5.5A, f=1MHz
Gate-Source charge	Q _{gs}	-	5.3	-		
Gate-Drain charge	Q _{gd}	-	8.8	-		
Turn-on delay time	t _{d(on)}	-	20	-	ns	T _j =25°C, V _{GS} =10V, I _D =5.5A, V _{DS} =400V, R _g =25Ω
Rise time	t _r	-	15	-		
Turn-off delay time	t _{d(off)}	-	74	-		
Fall time	t _f	-	43	-		
Gate resistance	R _G	-	2.0	-	Ω	V _{GS} =0V, V _{DS} =0V, f=1MHz



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CRJD390N65GC

SJMOS N-MOSFET 650V, 0.39Ω, 11A

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	0.5	0.84	1	V	$V_{GS}=0V, I_{SD}=5.5A$
Body Diode Reverse Recovery Time	t_{rr}	-	218	-	ns	$I_{sd}=5.5A$ $dI/dt=100A/us, V_{ds}=100V$
Body Diode Reverse Recovery Charge	Q_{rr}	-	2.35	-	uC	



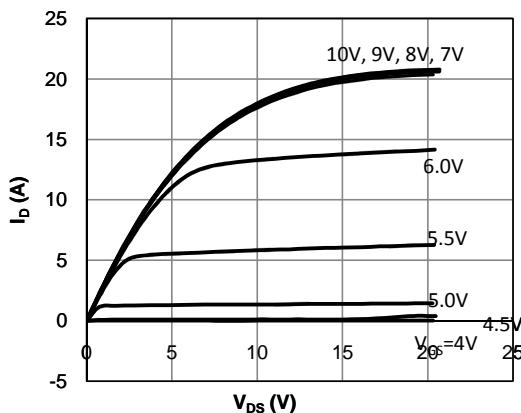
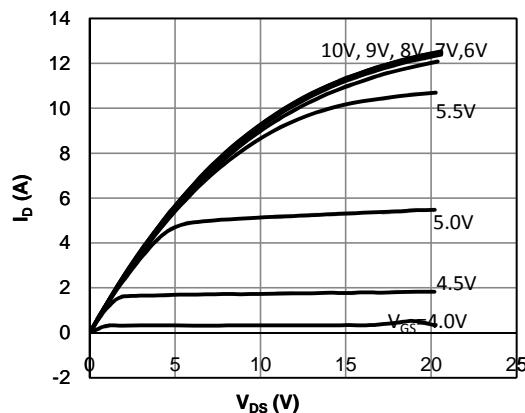
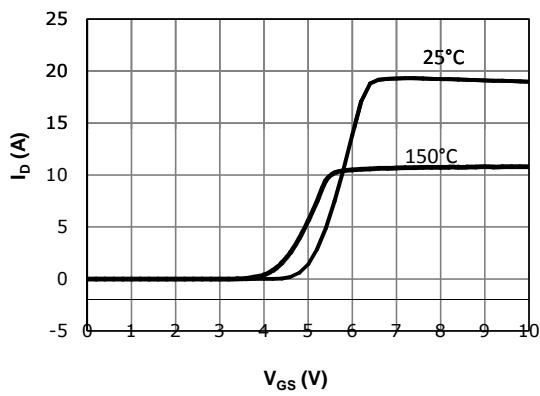
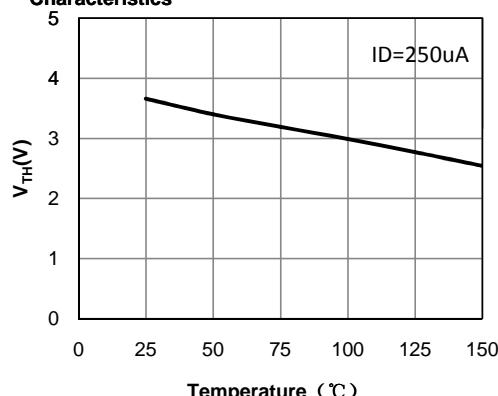
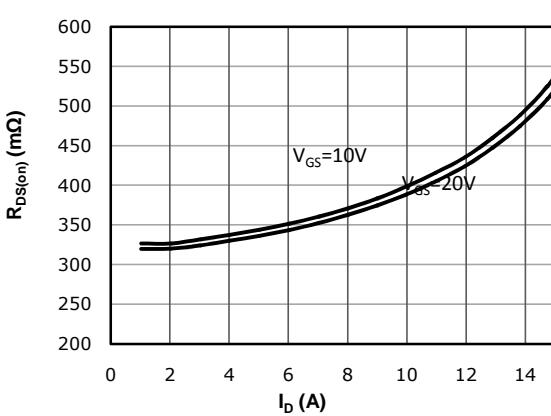
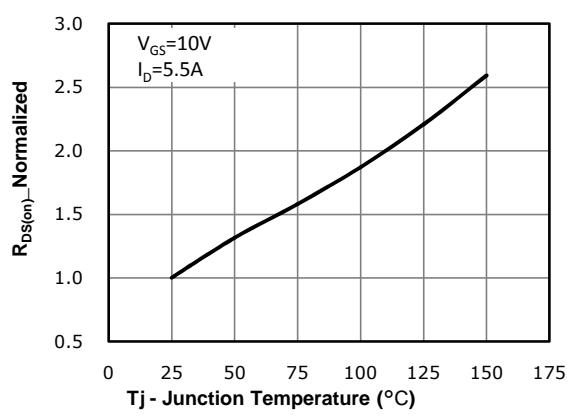
Typical Performance Characteristics
Fig 1. Output Characteristics ($T_j=25^\circ\text{C}$)

Fig 2. Output Characteristics ($T_j=150^\circ\text{C}$)

Fig 3: Transfer Characteristics

Fig 4: V_{TH} Vs T_j Temperature Characteristics

Fig 5: $R_{DS(on)}$ Vs I_D Characteristics ($T_c=25^\circ\text{C}$)

Fig 6: $R_{DS(on)}$ vs. Temperature


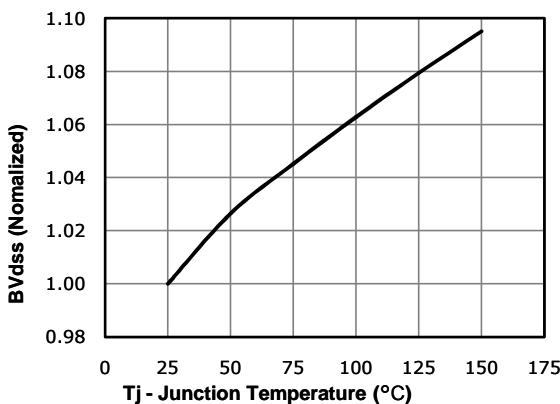
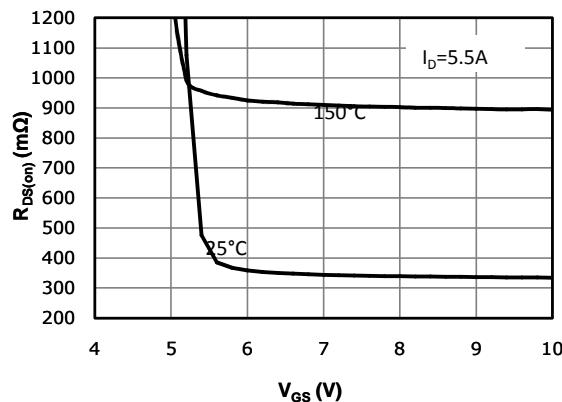
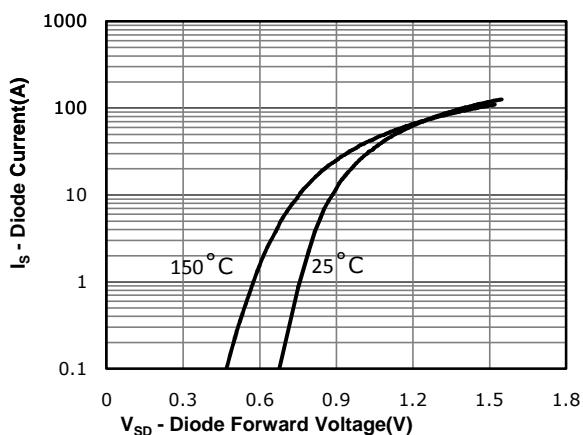
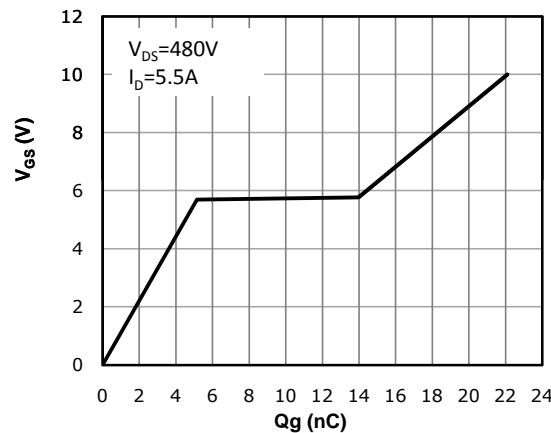
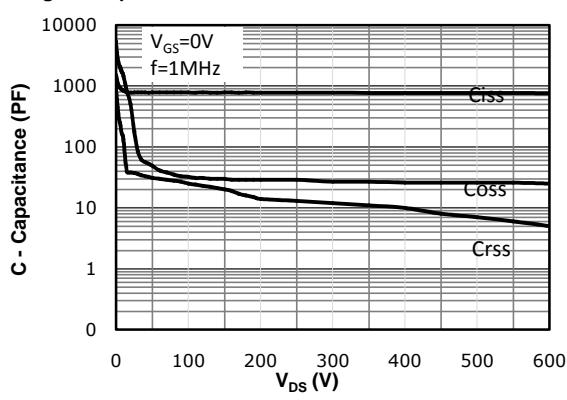
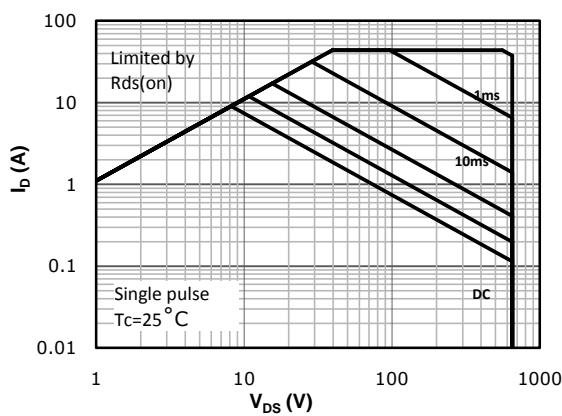
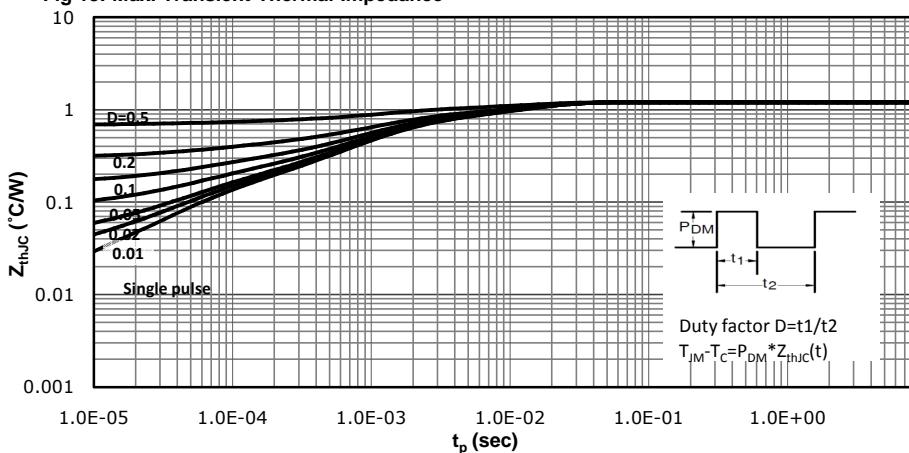
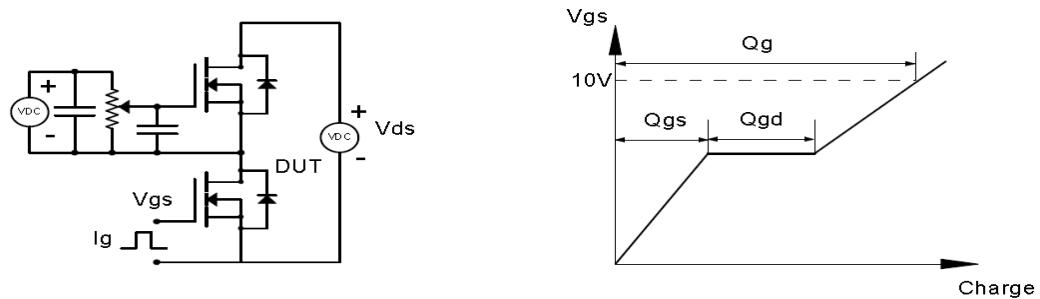
Fig 7: BV_{DSS} vs. Temperature

Fig 8: R_{d(on)} vs Gate Voltage

Fig 9: Body-diode Forward Characteristics

Fig 10: Gate Charge Characteristics

Fig 11: Capacitance Characteristics

Fig 12: Safe Operating Area


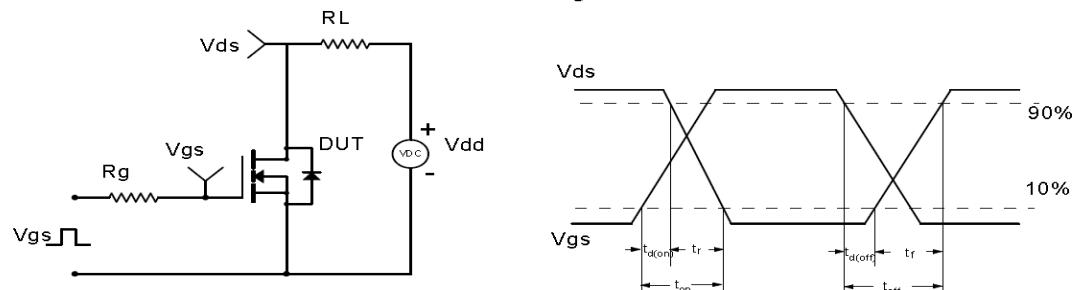
Fig 13: Max. Transient Thermal Impedance

Test Circuit & Waveform

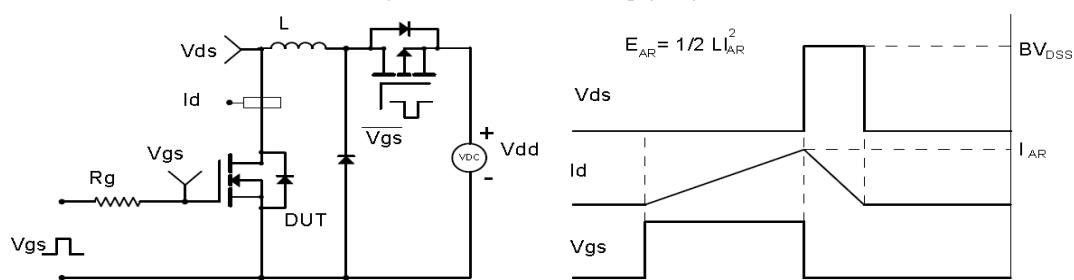
Gate Charge Test Circuit & Waveform



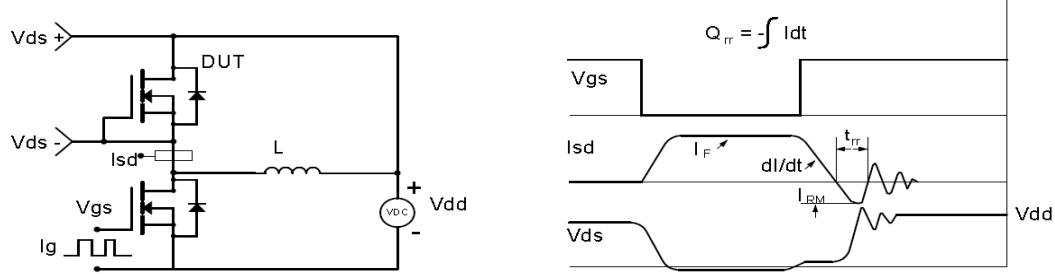
Resistive Switching Test Circuit & Waveforms

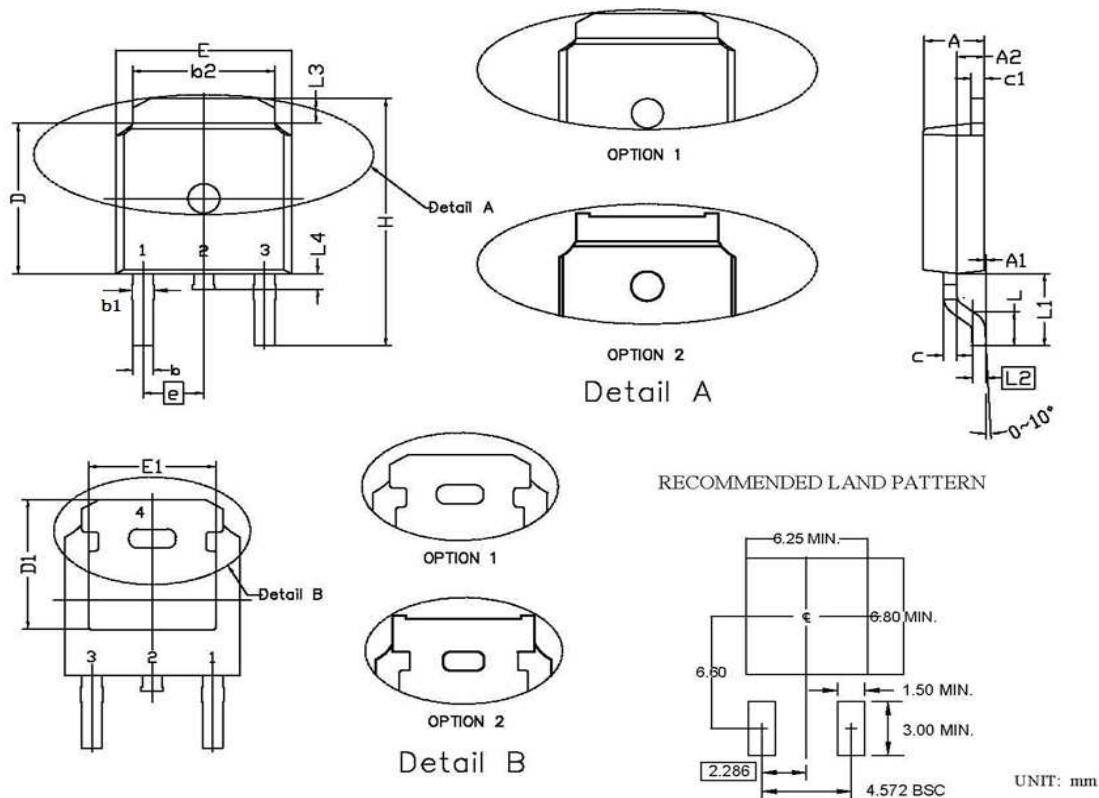


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO-252


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.15	2.45	0.085	0.096
A1	0.00	0.15	0.000	0.006
A2	0.76	1.36	0.030	0.054
b	0.60	0.91	0.024	0.036
b1	0.65	1.15	0.026	0.045
b2	5.00	5.64	0.197	0.222
c	0.45	0.61	0.018	0.024
c1	0.36	0.66	0.014	0.026
D	5.80	6.30	0.228	0.248
D1	5.00	6.00	0.197	0.236
e	2.29 BSC.		0.090 BSC.	
E	6.30	6.90	0.248	0.272
E1	4.55	5.30	0.179	0.209
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L1	2.92 REF		0.115 REF	
L2	0.36	0.66	0.014	0.026
L3	0.72	1.35	0.028	0.053
L4	0.60	1.20	0.024	0.047



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SJMOS N-MOSFET 650V, 0.39Ω, 11A

Revision History

Revison	Date	Major changes
1.0	2019-4-2	Release of formal version

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

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